

RHRU7540, RHRU7550, RHRU7560

Data Sheet April 1995 File Number 3945.1

75A, 400V - 600V Hyperfast Diodes

RHRU7540, RHRU7550 and RHRU7560 (TA49067) are hyperfast diodes with soft recovery characteristics ($t_{RR} < 55$ ns). They have half the recovery time of ultrafast diodes and are silicon nitride passivated ion-implanted epitaxial planar construction.

These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and hyperfast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

Ordering Information

PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RHRU7540	TO-218	RHRU7540
RHRU7550	TO-218	RHRU7550
RHRU7560	TO-218	RHRU7560

NOTE: When ordering, use the entire part number.

Features

•	Hyperfast with Soft Recovery<55ns
•	Operating Temperature +175°C
•	Reverse Voltage Up To600V

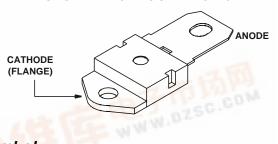
- Avalanche Energy Rated
- Planar Construction

Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

Package

SINGLE LEAD JEDEC STYLE TO-218



Symbol



Absolute Maximum Ratings T_C = +25°C, Unless Otherwise Specified

	RHRU7540	RHRU7550	RHRU7560	UNITS
Peak Repetitive Reverse Voltage	400	500	600	V
Working Peak Reverse VoltageVRWM	400	500	600	V
DC Blocking VoltageV _R	400	500	600	V
Average Rectified Forward Current $I_{F(AV)}$ ($T_{C} = +80^{\circ}C$)	75	75	75	Α
Repetitive Peak Surge CurrentIFSM (Square Wave, 20kHz)	150	150	150	Α
Nonrepetitive Peak Surge Current	750	750	750	Α
Maximum Power Dissipation	190	190	190	W
Avalanche Energy (See Figures 10 and 11)E _{AVL}	50	50	50	mj
Operating and Storage Temperature	-65 to +175	-65 to +175	-65 to +175	οС



RHRU7540, RHRU7550, RHRU7560

Electrical Specifications $T_C = +25^{\circ}C$, Unless Otherwise Specified

		RHRU7540		RHRU7550		RHRU7560					
SYMBOL	TEST CONDITION	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	UNITS
V _F	$I_F = 75A, T_C = +25^{\circ}C$	-	-	2.1	-	-	2.1	-	-	2.1	V
	I _F = 75A, T _C = +150 ^o C	-	-	1.7	-	-	1.7	-	-	1.7	V
I _R	$V_R = 400V, T_C = +25^{\circ}C$	-	-	500	-	-	-	-	-	-	μΑ
	$V_R = 500V, T_C = +25^{\circ}C$	-	-	-	-	-	500	-	-	-	μΑ
	$V_R = 600V, T_C = +25^{\circ}C$	-	-	-	-	-	-	-	-	500	μΑ
I _R	$V_R = 400V, T_C = +150^{\circ}C$	-	-	2.0	-	-	-	-	-	-	mA
	$V_R = 500V, T_C = +150^{\circ}C$	-	-	-	-	-	2.0	-	-	-	mA
	$V_R = 600V, T_C = +150^{\circ}C$	-	-	-	-	-	-	-	-	2.0	mA
t _{RR}	$I_F = 1A$, $dI_F/dt = 100A/\mu s$	-	-	55	-	-	55	-	-	55	ns
	I _F = 75A, dI _F /dt = 100A/μs	-	-	60	-	-	60	-	-	60	ns
t _A	I _F = 75A, dI _F /dt = 100A/μs	-	35	-	-	35	-	-	35	-	ns
t _B	I _F = 75A, dI _F /dt = 100A/μs	-	18	-	-	18	-	-	18	-	ns
Q _{RR}	I _F = 75A, dI _F /dt = 100A/μs	-	90	-	-	90	-	-	90	-	nC
CJ	$V_R = 10V, I_F = 0A$	-	200	-	-	200	-	-	200	-	pF
$R_{\theta JC}$		-	-	0.8	-	-	0.8	-	-	0.8	°C/W

DEFINITIONS

 V_F = Instantaneous forward voltage (pw = 300 μ s, D = 2%).

I_R = Instantaneous reverse current.

 t_{RR} = Reverse recovery time (See Figure 2), summation of t_{A} + t_{B} .

 t_A = Time to reach peak reverse current (See Figure 2).

 t_B = Time from peak I_{RM} to projected zero crossing of I_{RM} based on a straight line from peak I_{RM} through 25% of I_{RM} (See Figure 2).

Q_{RR} = Reverse recovery charge.

C_J = Junction Capacitance.

 $R_{\theta JC}$ = Thermal resistance junction to case.

 E_{AVL} = Controlled avalanche energy. (See Figures 10 and 11).

pw = pulse width.

D = duty cycle.

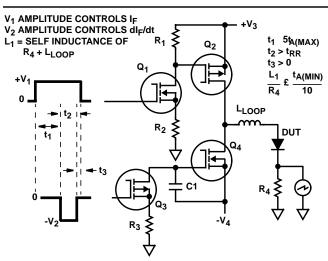


FIGURE 1. t_{RR} TEST CIRCUIT

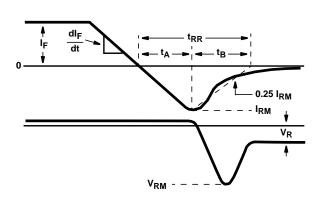


FIGURE 2. t_{RR} WAVEFORMS AND DEFINITIONS

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Typical Performance Curves

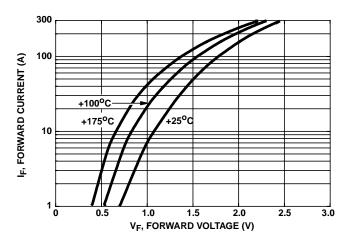


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD **VOLTAGE DROP**

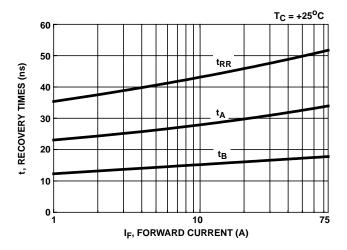


FIGURE 5. TYPICAL t_{RR} , t_{A} AND t_{B} CURVES vs FORWARD CURRENT AT +25°C

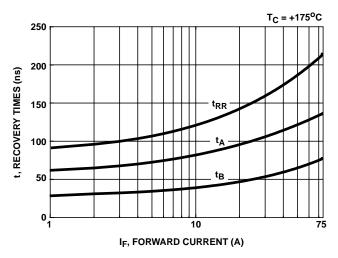


FIGURE 7. TYPICAL t_{RR} , t_{A} AND t_{B} CURVES vs FORWARD CURRENT AT +175 $^{\rm O}$ C

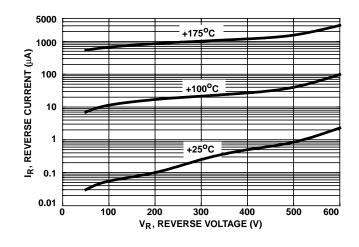


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE **VOLTAGE**

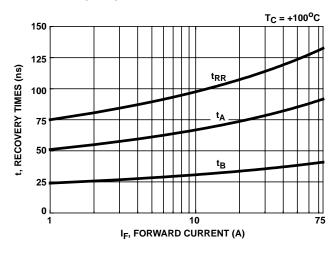


FIGURE 6. TYPICAL t_{RR} , t_{A} AND t_{B} CURVES vs FORWARD CURRENT AT +100 $^{\rm O}$ C

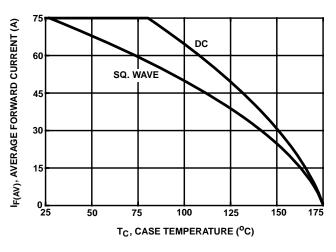


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

Typical Performance Curves (Continued)

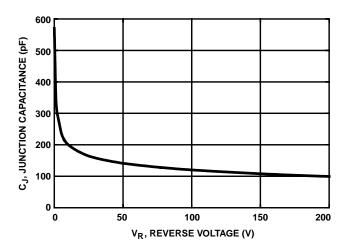


FIGURE 9. TYPICAL JUNCTION CAPACITANCE vs REVERSE VOLTAGE

Test Circuit and Waveforms

 $I_{MAX} = 1A$ L = 40mH $R < 0.1\Omega$ $E_{AVL} = 1/2LI^2 [V_{AVL}/(V_{AVL} - V_{DD})]$ Q1 AND Q2 ARE 1000V MOSFETs **130**Ω 1ΜΩ DUT Q_2 **CURRENT 130**Ω SENSE V_{DD} 12V

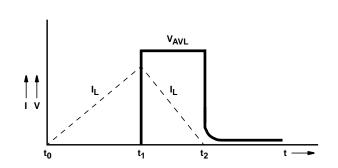


FIGURE 10. AVALANCHE ENERGY TEST CIRCUIT

FIGURE 11. AVALANCHE CURRENT AND VOLTAGE WAVEFORM

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Sales Office Headquarters

NORTH AMERICA

Intersil Corporation P. O. Box 883, Mail Stop 53-204 Melbourne, FL 32902

TEL: (321) 724-7000 FAX: (321) 724-7240

EUROPE

Intersil SA Mercure Center 100, Rue de la Fusee 1130 Brussels, Belgium TEL: (32) 2.724.2111

FAX: (32) 2.724.22.05

Intersil (Taiwan) Ltd. 7F-6, No. 101 Fu Hsing North Road Taipei, Taiwan Republic of China TEL: (886) 2 2716 9310 FAX: (886) 2 2715 3029